

Description

The invention relates to a transconductance circuit comprising

- a first and a second transistor of a first conductivity type having their bases coupled to input terminals for receiving an input signal and having their emitters connected to a common point by means of a first resistor, which common point is coupled to a first power-supply terminal by means of a current source, and
- a third transistor of the first conductivity type whose collector-emitter path is arranged between a second power-supply terminal and the common point and having its base coupled to a tapping of a voltage divider comprising two substantially identical second resistors arranged between the bases of the first and the second transistor.

Such a circuit arrangement is generally suitable for use in integrated circuits and is particularly suitable for those uses where a comparatively large input voltage range is required.

Such an arrangement is known from European Patent Application 0,157,447. In the absence of an input voltage most of the current from the current source flows through the third transistor, so that only a small current will flow through the first resistors and the first and the second transistor. When the input voltage increases the current through the third transistor decreases and the current through either the first or second transistor increases until the entire current from the current source flows through this transistor. As a result of the small quiescent current through the first resistors and the first and the second transistor this circuit has a very low input offset voltage. Moreover, since the current through the first and the second transistor increases as the input voltage increases the circuit has a substantial slew rate.

However, a drawback of this circuit is that it exhibits a comparatively large non-linearity, which is caused by the fact that for low input voltages the transconductance of the circuit is substantially twice as high as that for high input voltages. Indeed, for low input voltages both the first and the second transistor contribute to the signal output current, whereas for high input voltages only one of the transistors contributes to this current.

Therefore, it is an object of the invention to improve the linearity of the known transconductance circuit. According to the invention a transconductance circuit of the type defined in the opening paragraph is characterized in that the circuit further comprises

- a fourth and a fifth transistor of the first conductivity type, having their collector-emitter paths arranged in series with the collector-emitter paths of the first and the second transistor, having their bases coupled to a reference-voltage terminal, and having their collectors coupled to the output terminals for supplying an output signal, and
- a third resistor arranged between the emitters of the fourth and the fifth transistor.

For low input voltages the currents through the first and the second transistor and hence those through the fourth and the fifth transistor are comparatively small. The base-emitter resistances of the fourth and the fifth transistor are then comparatively high. A part of the signal current through the first and the second transistor consequently flows through the third resistor, causing the output signal current and hence the transconductance of the circuit to be reduced. For high input voltages and consequently comparatively large collector currents the base-emitter resistances are comparatively low, so that almost the entire signal current flows into the collectors of the fourth and the fifth transistor. As a result of this, comparatively high input voltages have hardly any influence on the transconductance of the circuit. The steps in accordance with the invention thus ensure that for low input voltages the transconductance is better in conformity with that for high input voltages, which improves the linearity of the circuit.

An embodiment of the circuit in accordance with the invention is characterized in that the circuit further comprises a sixth and a seventh transistor of a second conductivity type, having their collector-emitter paths arranged between the emitters of the first and the second transistor and the first power-supply terminal and having their bases coupled to the bases of the first and the second transistor. In the known circuit the input voltage range depends inter alia on the value of the current source, which dictates the maximum output current of the circuit. The current of this current source cannot be selected arbitrarily large because the quiescent current through the first resistors and the first and the second transistor and hence the input voltage offset will then increase. In the embodiment of the circuit in accordance with the invention the input voltage range is extended in that the sixth and the seventh transistor are turned on at high input voltages to supplement the current from the current source. In addition, the sixth and the seventh transistor protect the first and the second transistor against base-emitter breakdown owing to high negative base-emitter voltages.

The invention will now be described in more detail, by way of example, with reference to the accompanying drawing, in which

Fig. 1 shows the basic diagram of a transconductance circuit in accordance with the invention, and

Fig. 2 shows an embodiment of a transconductance circuit in accordance with the invention.

Fig. 1 shows the basic diagram of a transconductance circuit in accordance with the invention. The circuit comprises two NPN transistors T_1 and T_2 whose emitters are connected to a common point 2 via two substantially identical resistors R_1 , which common point is connected to the negative power-supply terminal 3, in the present case earth, by means of a current source 1. The bases of the transistors T_1 and T_2 are connected to input terminals 4 and 5 for receiving an input voltage V_i . Moreover, a voltage divider comprising two substantially identical resistors R_2 is arranged between the bases of the transistors T_1 and T_2 , the junction point between said resistors being connected to the base of an NPN transistor T_3 . The collector-emitter path of this transistor is arranged between the positive power-supply terminal 6 and the common point 2.

The collector-emitter paths of two NPN transistors T_4 and T_5 are arranged in series with the collector emitter paths of the transistors T_1 and T_2 . The bases of said transistors T_4 and T_5 are connected to a terminal 7 for a reference potential. A resistor R_3 is arranged between the emitters of the transistors T_4 and T_5 . The collectors of these transistors are connected to output terminals 8 and 9 from which the output currents of the circuit can be taken. The terminals 8 and 9 may be interconnected, for example by means of a differential-to-single-ended converter, such as a current mirror. However, alternatively the terminals 8 and 9 may be connected to any other active or passive load.

When the transistors T_4 and T_5 and the resistor R_3 are ignored, the circuit operates as follows. In the quiescent state the bias current through the transistors T_1 and T_2 is much smaller than that through the transistor T_3 as a result of the feedback resistors R_1 so that most of the current I_0 from the current source 1 flows through the last-mentioned transistor. As a result of the small bias currents the circuit has a very low input offset voltage. As the input voltage increases the current through the transistor T_3 decreases gradually to zero, and the current through, for example, the transistor T_1 increases gradually until the entire current I_0 flows through this transistor.

The maximum signal current which can be delivered by the circuit is equal to the difference between the collector currents of the transistors T_1 and T_2 . For high input voltages one of the transistors T_1 and T_2 is wholly or substantially cut off, so that only one of these transistors contributes to the output signal current. This current is inversely proportional to the sum of the resistance values of the resistors R_1 . For low input voltages both transistors carry equal signal currents of opposite phase and of a magnitude which is also inversely proportional to the sum of the resistance values of the resistors R_1 if the base-emitter resistances of the transistors T_1 and T_2 are ignored. Consequently, the maximum output current is substantially inversely proportional to the resistance value of the resistor R_1 . The transconductance of the circuit for low input voltages is therefore substantially twice as high as that for high input voltages. This input voltage which increases as the transconductance decreases leads to non-linearities of the output signal.

By means of the transistors T_4 and T_5 and the resistor R_3 the transconductance of the circuit for low input voltages is reduced, so that it more closely approximates to the transconductance for high input voltages. For low input voltages the base-emitter resistance of the transistors T_1 and T_2 will then be comparatively high because the bias currents are then small. Since the bias currents through the transistors T_4 and T_5 are equal these transistors also have comparatively high base-emitter resistances. If the value of the resistor R_3 is small relative to the value of said resistances a part of the signal current flowing in the collectors of the transistors T_1 and T_2 will flow through the resistor R_3 . The signal currents in the collectors of the transistors T_4 and T_5 are consequently smaller than those in the collectors of the transistors T_1 and T_2 . As a result of this the circuit will have a lower transconductance for small input voltages than the known circuit. For high input voltages the circuit is hardly influenced by the transistors T_4 and T_5 and the resistor R_3 . For high input voltages the base-emitter resistances of the transistors T_4 and T_5 are low relative to the resistance value of the resistor R_3 because the bias currents flowing through these transistors are then larger. As a consequence, the signal current flowing in the collectors of the transistors T_4 and T_5 will be substantially equal to that in the collectors of the transistors T_1 and T_2 .

For a specific current I_0 of the current source 1 the resistance value of the resistor R_3 for an optimum linearity of the circuit can be computed as follows. For high positive input voltages V_{in} the collector signal current of the transistor T_4 complies with:

$$I_{cT4} \approx I_{cT1} = V_{in}/2R_1 \quad (1)$$

The transistor T_2 is then substantially cut off, so that:

$$I_{cT5} \approx I_{cT2} = 0 \quad (2)$$

Obviously, the situation is reversed for high negative input voltages. Consequently, the difference between the two collector currents complies with:

$$I_{CT4} - I_{CT5} \approx V_{in}/2R_1$$

For low input voltages both transistors T_1 and T_2 carry a signal current. The signal current in the collector of the transistor T_1 complies with:

$$I_{CT1} = s \cdot V_{beT1} = \frac{s \cdot V_{in}}{2(1+s \cdot R_1)} \quad (3)$$

and that of the transistor T_2 complies with:

$$I_{CT2} = s V_{beT2} = -\frac{s \cdot V_{in}}{2(1+s \cdot R_1)} \quad (4)$$

where s is the transconductance and V_{be} is the base-emitter voltage of the relevant transistor. If for low input voltages the transconductance of the circuit must be equal to that for large input voltages this means that

$$I_{CT4} = s \cdot V_{beT4} = V_{in}/4R_1 \quad (5)$$

and

$$I_{CT5} = s \cdot V_{beT5} = V_{in}/4R_1 \quad (6)$$

Since the collector current of the transistor T_1 is equal to the sum of the collector current of the transistor T_4 and the current through the resistor R_3 this means that:

$$I_{CT1} = \frac{s \cdot V_{in}}{2(1+s \cdot R_1)} + \frac{V_{beT4} - V_{beT5}}{R_3} \quad (7)$$

or

$$\frac{s \cdot V_{in}}{2(1+s \cdot R_1)} = \frac{V_{in}}{4R_1} + \frac{V_{in}}{2sR_1 \cdot R_3} \quad (8)$$

It follows that for an optimum value of the resistor R_3 the following requirement must be met:

$$R_3 = \left(\frac{s^2 R_1}{1+sR_1} - \frac{s}{2} \right)^{-1} \quad (9)$$

The transconductance $s = qI_1/kT$, where I_1 is the quiescent current through the transistors T_1 and T_2 , k is Boltzmann's constant, q is the elementary charge and T is the absolute temperature. The magnitude of the current I_1 can be derived simply from the voltage equation for the loop comprising the base-emitter junctions of the transistors T_1 and T_3 and the resistors R_1 and R_2 and from the equation for the sum of the currents through the transistors T_1 , T_2 and T_3 , which is equal to the current I_0 of the current source 1.

Since the transconductance s is inversely proportional to the absolute temperature the current I_1 and hence the current I_0 of the current source 1 should preferably increase as a direct proportional function of the absolute temperature in order to achieve an optimum value of the resistance over a wide temperature range. Such PTAT current sources (PTAT = Proportional To Absolute Temperature) are generally known and require no further explanation. Such a current source is shown, for example, on page 283, Fig. 425 in the book "Analysis and Design of Analog Integrated Circuits", 1984.

In Fig. 2, which shows an embodiment of the circuit in accordance with the invention, identical parts bear the same reference numerals as in Fig. 1. In this circuit the emitters of the transistors T_1 and T_2 are

connected to the negative power-supply terminal 3 by means of the collector-emitter paths of the PNP transistors T_6 and T_7 . The base of the transistor T_6 is connected to the base of the transistor T_1 and the base of the transistor T_7 is connected to the base of the transistor T_2 . In the circuit shown in Fig. 1 the effective input-voltage range is dictated by the current I_0 from the current source 1. This is because the current I_0 is the maximum output current of the circuit. The current I_0 cannot be selected too large because otherwise the input offset voltage will increase excessively. In the circuit shown in Fig. 2 the input-voltage range is extended in that for high input voltages the transistors T_6 and T_7 are turned on to increase the bias current of the circuit. In addition, the transistors T_6 and T_7 protect the transistors T_1 and T_2 against emitter base breakdown in the case of high voltages across the emitter base junctions of these transistors.

The invention is not limited to the embodiments shown herein. For example, the circuits shown may be equipped with transistors of opposite conductivity types. Moreover, the transistors may have either equal or unequal emitter areas.

In addition, it is possible to merely increase the input-voltage range of the circuit and to refrain from the linearity correction if the latter aspect is not important.

Claims

1. A transconductance circuit comprising

- a first and a second transistor of a first conductivity type having their bases coupled to input terminals for receiving an input signal and having their emitters connected to a common point by means of a first resistor, which common point is coupled to a first power-supply terminal by means of a current source, and
- a third transistor of the first conductivity type whose collector-emitter path is arranged between a second power-supply terminal and the common point and having its base coupled to a tapping of a voltage divider comprising two substantially identical second resistors arranged between the bases of the first and the second transistor, characterized in that the circuit further comprises
- a fourth and a fifth transistor of the first conductivity type, having their collector-emitter paths arranged in series with the collector-emitter paths of the first and the second transistor, having their bases coupled to a reference-voltage terminal, and having their collectors coupled to the output terminals for supplying an output signal, and
- a third resistor arranged between the emitters of the fourth and the fifth transistor.

2. A transconductance circuit as claimed in Claim 1, characterized in that the circuit further comprises a sixth and a seventh transistor of a second conductivity type, having their collector-emitter paths arranged between the emitters of the first and the second transistor and the first power-supply terminal and having their bases coupled to the bases of the first and the second transistor.

3. A transconductance circuit as claimed in Claim 1 or 2, characterized in that the current source is adapted to supply a current with a positive temperature coefficient.

Patentansprüche

1. Transkonduktanzschaltung mit

- einem ersten und einem zweiten Transistor eines ersten Leitungstyps, deren Basen mit Eingangsklemmen für den Empfang eines Eingangssignals gekoppelt und deren Emitter mit Hilfe eines ersten Widerstandes mit einem gemeinsamen Punkt verbunden sind, welcher letzterer über eine Stromquelle mit einer ersten Versorgungsanschlußklemme gekoppelt ist, und
- einem dritten Transistor des ersten Leitungstyps, dessen Kollektor-Emitter-Strecke zwischen einer zweiten Versorgungsanschlußklemme und dem gemeinsamen Punkt angeordnet ist und dessen Basis mit einem Abgreifpunkt eines Spannungsteilers aus zwei nahezu identischen, zwischen der Basis des ersten und der Basis des zweiten Transistors angeordneten zweiten Widerständen gekoppelt ist, dadurch gekennzeichnet, daß die Schaltung außerdem folgendes umfaßt
- einen vierten und einen fünften Transistor des ersten Leitungstyps, deren Kollektor-Emitter-Strecken mit den Kollektor-Emitter-Strecken des ersten und des zweiten Transistors in Reihe geschaltet sind und deren Basen mit einer Bezugsspannungsanschlußklemme gekoppelt sind und deren Kollektoren zur Lieferung eines Ausgangssignals mit den Ausgangsklemmen gekoppelt



connected to the negative power-supply terminal 3 by means of the collector-emitter paths of the PNP transistors T_6 and T_7 . The base of the transistor T_6 is connected to the base of the transistor T_1 and the base of the transistor T_7 is connected to the base of the transistor T_2 . In the circuit shown in Fig. 1 the effective input-voltage range is dictated by the current I_0 from the current source 1. This is because the current I_0 is the maximum output current of the circuit. The current I_0 cannot be selected too large because otherwise the input offset voltage will increase excessively. In the circuit shown in Fig. 2 the input-voltage range is extended in that for high input voltages the transistors T_6 and T_7 are turned on to increase the bias current of the circuit. In addition, the transistors T_6 and T_7 protect the transistors T_1 and T_2 against emitter base breakdown in the case of high voltages across the emitter base junctions of these transistors.

The invention is not limited to the embodiments shown herein. For example, the circuits shown may be equipped with transistors of opposite conductivity types. Moreover, the transistors may have either equal or unequal emitter areas.

In addition, it is possible to merely increase the input-voltage range of the circuit and to refrain from the linearity correction if the latter aspect is not important.

Claims

1. A transconductance circuit comprising
 - a first and a second transistor of a first conductivity type having their bases coupled to input terminals for receiving an input signal and having their emitters connected to a common point by means of a first resistor, which common point is coupled to a first power-supply terminal by means of a current source, and
 - a third transistor of the first conductivity type whose collector-emitter path is arranged between a second power-supply terminal and the common point and having its base coupled to a tapping of a voltage divider comprising two substantially identical second resistors arranged between the bases of the first and the second transistor, characterized in that the circuit further comprises
 - a fourth and a fifth transistor of the first conductivity type, having their collector-emitter paths arranged in series with the collector-emitter paths of the first and the second transistor, having their bases coupled to a reference-voltage terminal, and having their collectors coupled to the output terminals for supplying an output signal, and
 - a third resistor arranged between the emitters of the fourth and the fifth transistor.
2. A transconductance circuit as claimed in Claim 1, characterized in that the circuit further comprises a sixth and a seventh transistor of a second conductivity type, having their collector-emitter paths arranged between the emitters of the first and the second transistor and the first power-supply terminal and having their bases coupled to the bases of the first and the second transistor.
3. A transconductance circuit as claimed in Claim 1 or 2, characterized in that the current source is adapted to supply a current with a positive temperature coefficient.

Patentansprüche

1. Transkonduktanzschaltung mit
 - einem ersten und einem zweiten Transistor eines ersten Leitungstyps, deren Basen mit Eingangsklemmen für den Empfang eines Eingangssignals gekoppelt und deren Emittter mit Hilfe eines ersten Widerstandes mit einem gemeinsamen Punkt verbunden sind, welcher letzterer über eine Stromquelle mit einer ersten Versorgungsanschlußklemme gekoppelt ist, und
 - einem dritten Transistor des ersten Leitungstyps, dessen Kollektor-Emitter-Strecke zwischen einer zweiten Versorgungsanschlußklemme und dem gemeinsamen Punkt angeordnet ist und dessen Basis mit einem Abgreifpunkt eines Spannungsteilers aus zwei nahezu identischen, zwischen der Basis des ersten und der Basis des zweiten Transistors angeordneten zweiten Widerständen gekoppelt ist, dadurch gekennzeichnet, daß die Schaltung außerdem folgendes umfaßt
 - einen vierten und einen fünften Transistor des ersten Leitungstyps, deren Kollektor-Emitter-Strecken mit den Kollektor-Emitter-Strecken des ersten und des zweiten Transistors in Reihe geschaltet sind und deren Basen mit einer Bezugsspannungsanschlußklemme gekoppelt sind und deren Kollektoren zur Lieferung eines Ausgangssignals mit den Ausgangsklemmen gekoppelt



sind, und

- einen zwischen den Emittern des vierten und des fünften Transistors angeordneten dritten Widerstand.

2. Transkonduktanzschaltung nach Anspruch 1, dadurch gekennzeichnet, daß die Schaltung außerdem einen sechsten und einen siebten Transistor eines zweiten Leitungstyps umfaßt, wobei deren Kollektor-Emitter-Strecken zwischen den Emittern des ersten und des zweiten Transistors und der ersten Versorgungsanschlußklemme angeordnet sind und deren Basen mit den Basen des ersten und des zweiten Transistors gekoppelt sind.

3. Transkonduktanzschaltung nach Anspruch 1 oder 2, dadurch gekennzeichnet, daß die Stromquelle für die Lieferung eines Stromes mit positivem Temperaturkoeffizienten eingerichtet ist.

Revendications

1. Circuit de transconductance comprenant :

- un premier et un deuxième transistor d'un premier type de conductivité dont les bases sont couplées à des bornes d'entrée pour recevoir un signal d'entrée et dont les émetteurs sont connectés à un point commun au moyen d'une première résistance, le point commun étant couplé à une première borne d'alimentation électrique au moyen d'une source de courant, et
- un troisième transistor du premier type de conductivité dont le trajet collecteur-émetteur est disposé entre une seconde borne d'alimentation électrique et le point commun et dont la base est couplée à une prise d'un diviseur de tension comprenant deux secondes résistances en substance identiques disposées entre les bases du premier et du deuxième transistor, caractérisé en ce que le circuit comprend, en outre,
- un quatrième et un cinquième transistor du premier type de conductivité, dont les trajets collecteur-émetteur sont disposés en série avec les trajets collecteur-émetteur du premier et du deuxième transistor, dont les bases sont couplées à une borne de tension de référence et dont les collecteurs sont couplés aux bornes de sortie pour fournir un signal de sortie, et
- une troisième résistance disposée entre les émetteurs du quatrième et du cinquième transistor.

2. Circuit de transconductance suivant la revendication 1, caractérisé en ce qu'il comprend, en outre, un sixième et un septième transistor d'un second type de conductivité, dont les trajets collecteur-émetteur sont disposés entre les émetteurs du premier et du deuxième transistor et la première borne d'alimentation électrique et dont les bases sont couplées aux bases du premier et du deuxième transistor.

3. Circuit de transconductance suivant la revendication 1 ou 2, caractérisé en ce que la source de courant est à même de fournir un courant avec un coefficient de température positif.